

| | Type | Hits | Search Text | DBs | Time Stamp | Comments | Error Definition |
|----|------|------|---|---|------------------|----------|------------------|
| 22 | BRS | 1 | electric adj field adj reducing adj layer | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/12 16:00 | | |
| 23 | BRS | 1424 | (electric adj field) near10 (reduc\$6 near10 layer) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/12 16:02 | | |
| 24 | BRS | 321 | electric adj field adj relaxation | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/13 04:08 | | |
| 25 | BRS | 305 | (kozuka near2 hiraki) or (sugawa near2 shigetoshi) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/13 07:57 | | |
| 26 | BRS | 37 | ((kozuka near2 hiraki) or (sugawa near2 shigetoshi)) and (electric adj field) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/13 06:52 | | |
| 27 | BRS | 27 | (hole and electron) adj (injection) adj (inhibiting or blocking) adj (layer or region) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/13 07:34 | | |
| 28 | BRS | 17 | ((injection) adj (inhibiting or blocking) adj (layer or region)) and ((conduction and valence) adj band) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/13 07:51 | | |
| 29 | BRS | 168 | level near10 equal near10 ((valence or conduction) adj band) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/13 07:51 | | |
| 30 | BRS | 1 | 6127692.URPN. | USPAT | 2002/12/13 07:52 | | |
| 31 | BRS | 11 | ((kozuka near2 hiraki) or (sugawa near2 shigetoshi)) and (valence and conduction) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/13 07:58 | | |
| 32 | BRS | 11 | ((kozuka near2 hiraki) or (sugawa near2 shigetoshi)) and ((valence and conduction) near2 band) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/13 08:08 | | |
| 33 | BRS | 15 | ("4169273" "4571624" "4745488" "5043719" "5060040" "5233442" "5262850" "5272548" "5288988" "5317406" "5335094" "5420452" "5463420" "5812109" "5999150"),PN. | USPAT | 2002/12/13 08:11 | | |
| 34 | BRS | 0 | canon and (electron adj injection adj inhibiting) and (valence adj band) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/13 08:21 | | |
| 35 | BRS | 4 | canon and (electron adj injection adj inhibiting) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/13 11:48 | | |
| 36 | BRS | 0 | (monocrystalline and polycrystalline and microcrystalline) near10 substrate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/13 11:50 | | |
| 37 | BRS | 134 | (monocrystalline and polycrystalline) near10 substrate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/13 11:54 | | |
| 38 | BRS | 677 | (microcrystalline) near10 substrate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/13 12:10 | | |
| 39 | BRS | 27 | ((monocrystalline) near10 substrate) and 348/\$.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/13 11:55 | | |
| 40 | BRS | 2 | ((microcrystalline) near10 substrate) and 348/\$.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/13 11:55 | | |
| 41 | BRS | 45 | ((polycrystalline) near10 substrate) and 348/\$.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/13 11:55 | | |
| 42 | BRS | 265 | (microcrystalline near10 silicon) near10 substrate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/13 12:19 | | |
| 43 | BRS | 47 | (microcrystalline near10 silicon near10 polycrystalline) near10 substrate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/13 12:20 | | |